

N-Channel 200-V (D-S) MOSFET

Key Features:

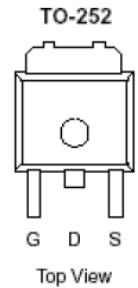
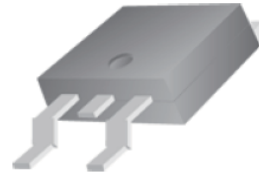
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits



RoHS
COMPLIANT
HALOGEN
FREE



PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
200	600 @ $V_{GS} = 10V$	7.5
	750 @ $V_{GS} = 4.5V$	6.7

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	7.5	A
Pulsed Drain Current ^b	I_{DM}	30	
Continuous Source Current (Diode Conduction) ^a	I_S	40	A
Power Dissipation ^a	P_D	50	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

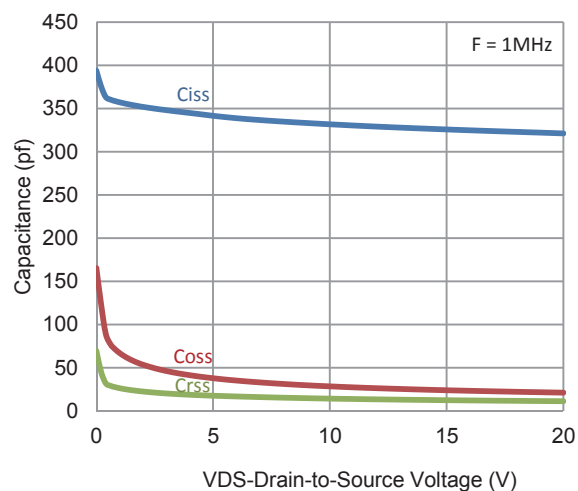
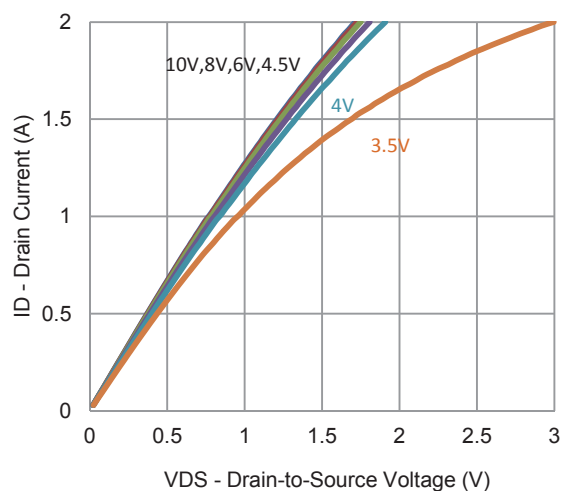
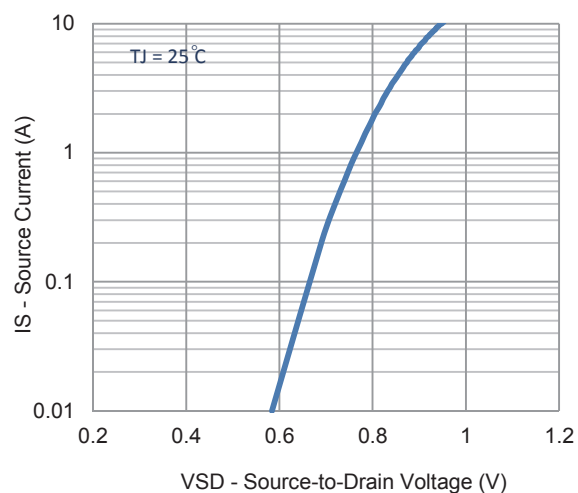
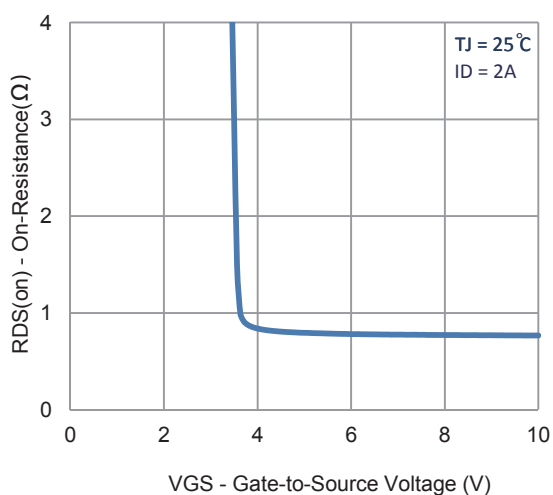
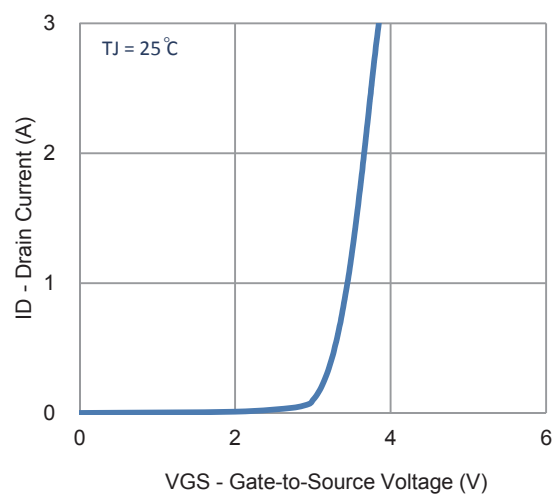
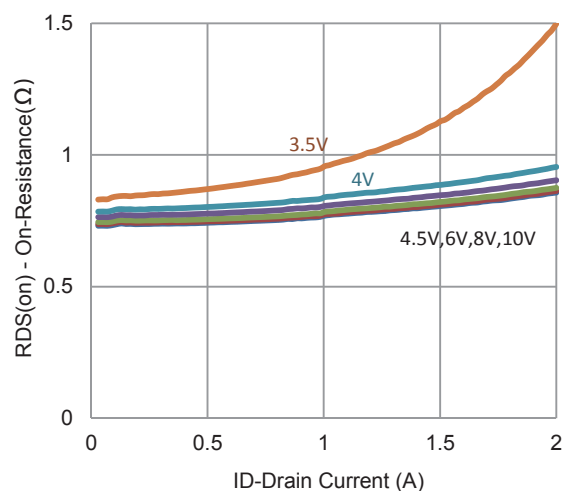
Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

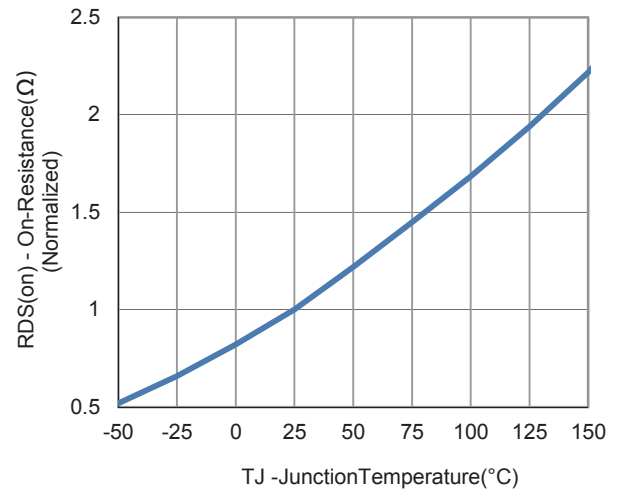
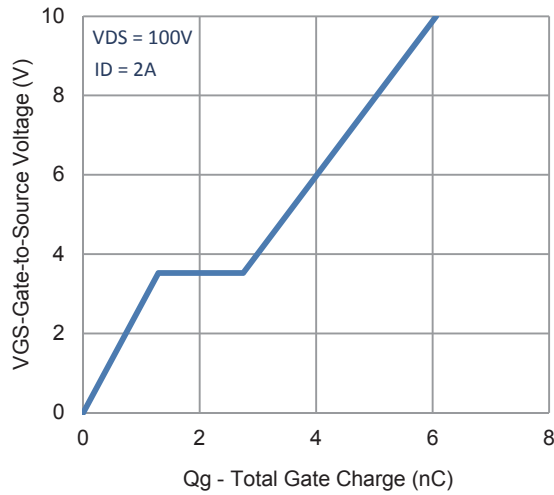
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 160 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 160 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	12			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 2 A$			600	m Ω
		$V_{GS} = 4.5 V, I_D = 1.6 A$			750	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 V, I_D = 2 A$		16		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 20 A, V_{GS} = 0 V$		0.9		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 100 V, V_{GS} = 4.5 V,$ $I_D = 2 A$		3.2		nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 100 V, R_L = 50 \Omega, I_D = 2 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		5		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			13		
Fall Time	t_f			5		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 Mhz$		325		pF
Output Capacitance	C_{oss}			23		
Reverse Transfer Capacitance	C_{rss}			12		

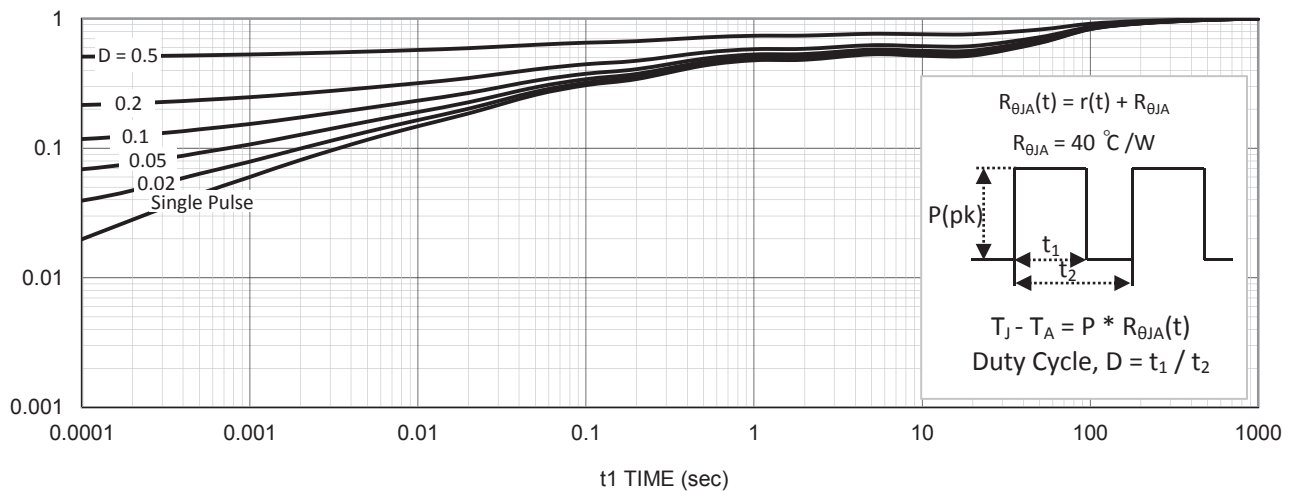
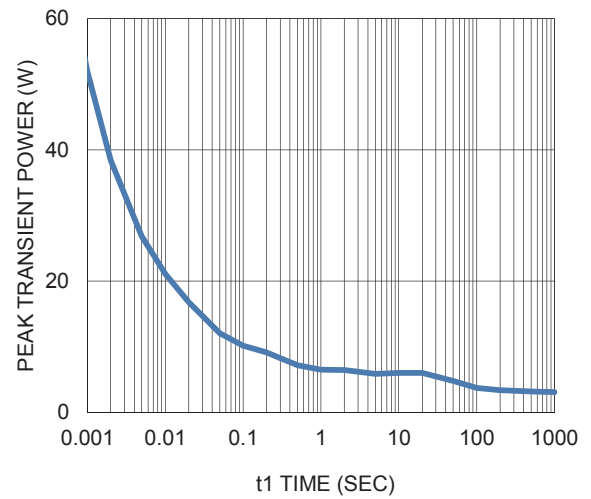
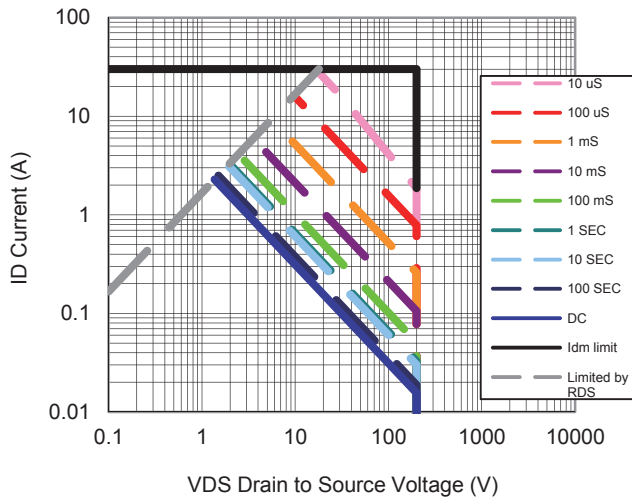
Typical Electrical Characteristics



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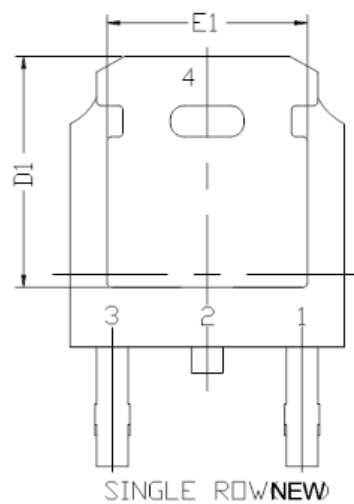
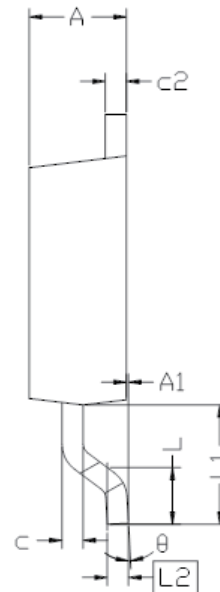
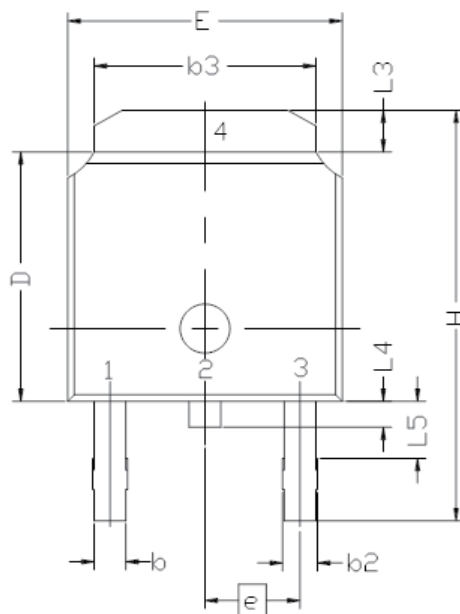


8. Normalized On-Resistance Vs Junction Temperature



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
θ	0°	--	10°

Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.